FAIRCHILD SEMICONDUCTOR TM

August 2001

FDP2570/FDB2570

150V N-Channel PowerTrench® MOSFET

General Description

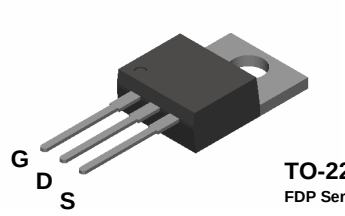
This N-Channel MOSFET has been designed specifically for switching on the primary side in the isolated DC/DC converter application. Any application requiring a 150V MOSFETs with low on-resistance and fast switching will benefit.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $RDS_{(ON)}$ specifications.

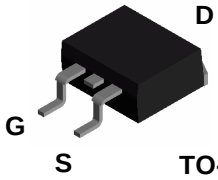
The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

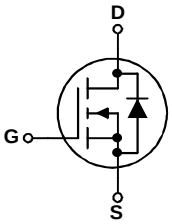
- 22 A, 150 V. $R_{DS(ON)}$ = 80 mΩ @ V_{GS} = 10 V
  $R_{DS(ON)}$ = 90 mΩ @ V_{GS} = 6 V
- Low gate charge (40nC typical)
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- 175°C maximum junction temperature rating



TO-220
FDP Series



TO-263AB
FDB Series



Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		150	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Drain Current – Continuous	(Note 1)	22	A
	– Pulsed	(Note 1)	50	A
P_D	Total Power Dissipation @ T_C = 25°C		93	W
	Derate above 25°C		0.63	W°/C
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–65 to +175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB2570	FDB2570	13''	24mm	800 units
FDP2570	FDP2570	Tube	n/a	45 units

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Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 1)						
W_{DSS}	Single Pulse Drain-Source Avalanche Energy	V_{DD} = 75 V, I_D = 11 A			375	mJ
I_{AR}	Maximum Drain-Source Avalanche Current				11	A
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		154		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120 V, V_{GS} = 0 V			1	µA
I_{GSSF}	Gate–Body Leakage, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	V_{GS} = –20 V, V_{DS} = 0 V			–100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	2.6	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		–7		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = 10 V, I_D = 11 A V_{GS} = 6.0 V, I_D = 10 A V_{GS} = 10 V, I_D = 11 A, T_J = 125°C		61 63 127	80 90 175	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = 10 V, V_{DS} = 10 V	25			A
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 11 A		39		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 75 V, V_{GS} = 0 V, f = 1.0 MHz		1911		pF
C_{oss}	Output Capacitance			106		pF
C_{rss}	Reverse Transfer Capacitance			33		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 75 V, I_D = 1 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		12	22	ns
t_r	Turn–On Rise Time			5	10	ns
$t_{d(off)}$	Turn–Off Delay Time			33	53	ns
t_f	Turn–Off Fall Time			23	37	ns
Q_g	Total Gate Charge	V_{DS} = 75 V, I_D = 11 A, V_{GS} = 10 V		40	56	nC
Q_{gs}	Gate–Source Charge			7		nC
Q_{gd}	Gate–Drain Charge			12		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				22	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 11 A (Note 2)		0.83	1.3	V

Notes:

1. Calculated continuous current based on maximum allowable junction temperature.

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics

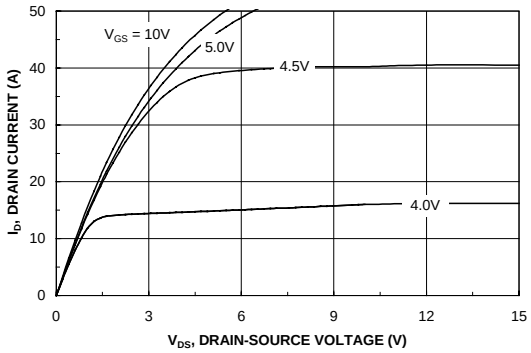


Figure 1. On-Region Characteristics.

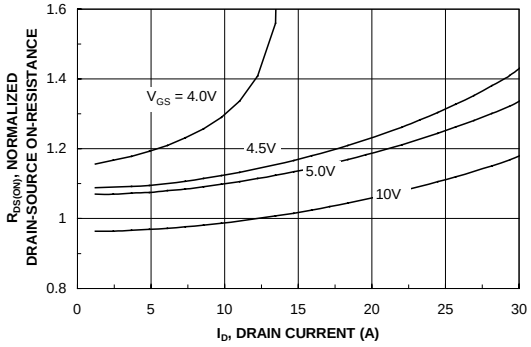


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

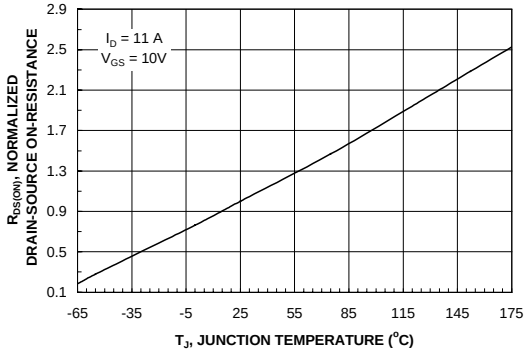


Figure 3. On-Resistance Variation with Temperature.

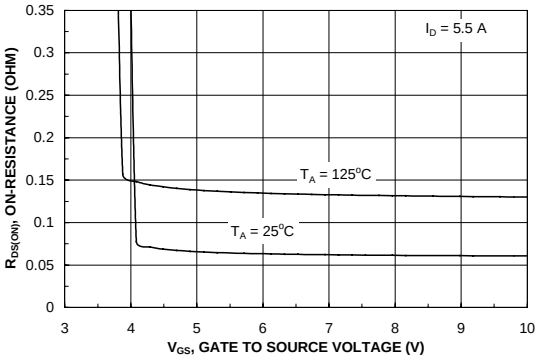


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

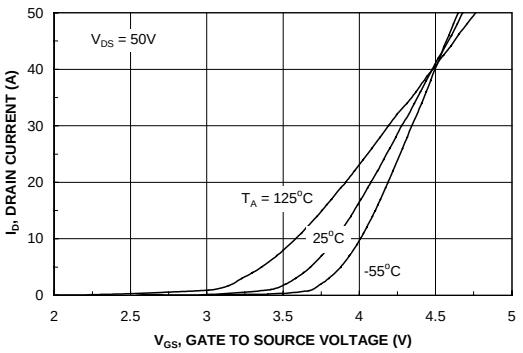


Figure 5. Transfer Characteristics.

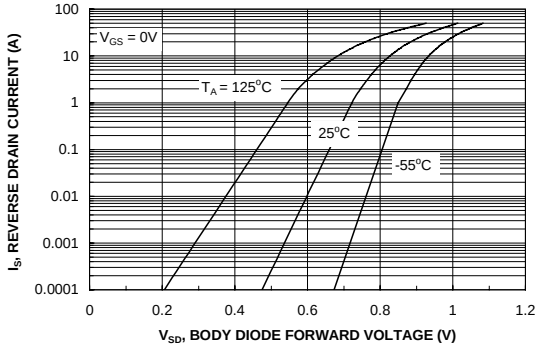


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

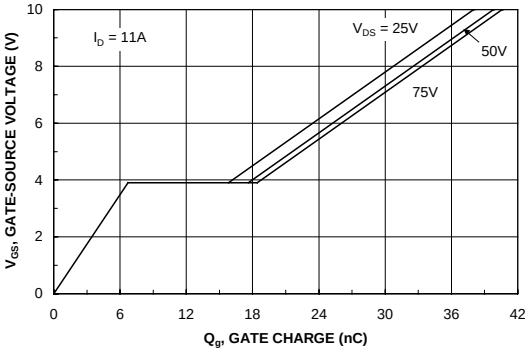


Figure 7. Gate Charge Characteristics.

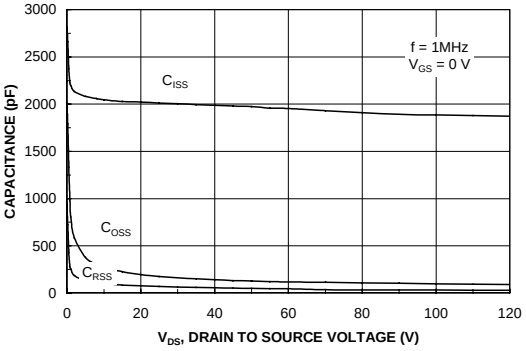


Figure 8. Capacitance Characteristics.

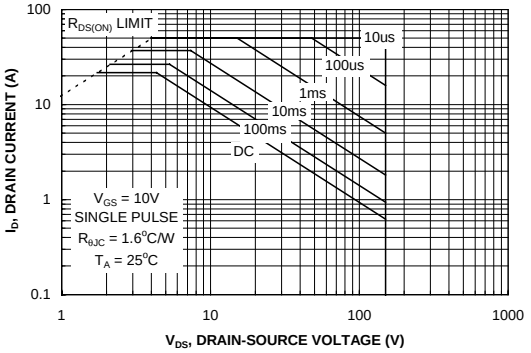


Figure 9. Maximum Safe Operating Area.

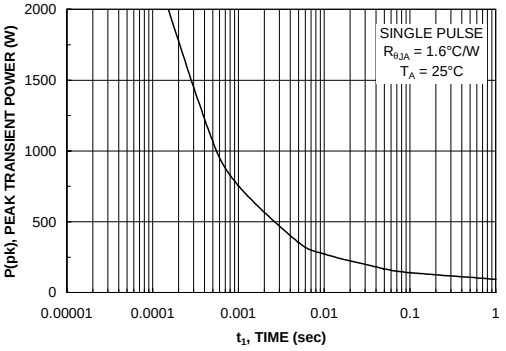


Figure 10. Single Pulse Maximum Power Dissipation.

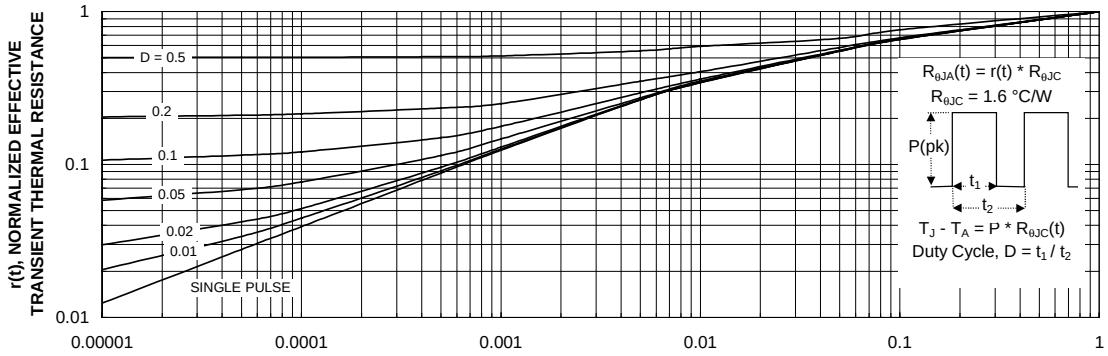


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1.
Transient thermal response will change depending on the circuit board design.

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